



Revision 0.72

2023-10-25



SINGLE FREQUENCY LASER External Cavity Diode Laser

Product	Application
780 nm mini-ECL Laser	Spectroscopy (Rb D2 line)
with hermetic 14-Pin Butterfly Housing (RoHS compliant)	Metrology
including Monitor Diode, Thermoelectric Cooler and Thermistor	Quantum Technology
with integrated Beam Collimation	



Absolute Maximum Ratings

General Product Information

Symbol	Unit	min	typ	max
Ts		-40		85
T_C	°C	-40		85
T_{chip}	°C	0		50
I _F	mA			200
V_R	V			2
P_{opt}	mW			100
I _{TEC}	Α			1.1
V_{TEC}	V			2.8
	T _S T _C T _{chip} I _F V _R P _{opt} I _{TEC}	$\begin{array}{ccc} T_{S} & & \\ T_{C} & ^{\circ}C \\ T_{Chip} & ^{\circ}C \\ I_{F} & mA \\ V_{R} & V \\ P_{opt} & mW \\ I_{TEC} & A \\ \end{array}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _{case}	°C	-20		65
Operational Temperature at Chip	T_{chip}	°C	5		45
Forward Current	I _F	mA			180
Output Power	P_{opt}	mW	20		80

Measurement Conditions / Comments			
measured by integrated Thermistor			

Characteristics = 25° C at BOL

Parameter	Cumphal	Llait		to en	
raianietei	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm	779	780	781
Target Wavelength	λ_{T}	nm		780.24	
Linewidth	$\Delta\lambda$	MHz		0.1	0.3
Mode-hop free Tuning Range	$\Delta \lambda_{tune}$	pm		20	
Output Power	P_{opt}	mW			80
Sidemode Suppression Ratio	SMSR	dB	30	50	
Temp. Coefficient of Wavelength	$d\lambda/dT$	nm/K		0.008	
Current Coefficient of Wavelength	$d\lambda/dI$	nm/mA		0.001	

Measurement Conditions / Comments				
reached within TLD = 5° C 45° C				
measured in the time scale of 1 ms				
By current tuning, at target wavelength				
Popt = 80 mW				



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Thermoelectric Cooler

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Characteristics	= 25° C at BOL				
Parameter	Symbol	Unit	min	typ	max
Laser Current	I _{LD}	mA			180
Slope Efficiency	η	mW/mA	0.6	8.0	1
Threshold Current	I _{th}	mA			70
Divergence parallel	$\Theta_{ }$	mrad		2	
Divergence perpendicular	Θ_{\perp}	mrad		2	
Beam Diameter horizontal	d	mm		1	1.2
Beam Diameter vertical	$d_{\!\perp}$	mm		8.0	1.2
Degree of Polarization	DOP	%		90	

Measurement Conditions / Comments

parallel to the base plate of the housing (see p. 3)
perpendicular to base plate of the housing (see p. 3)
parallel to the base plate of the housing (see p. 3)
perpendicular to base plate of the housing (see p. 3)
Popt = 80 mW; E field perpendicular to the base plate

Parameter	Symbol Unit	min	typ	max
Monitor Detector Responsivity	I _{mon} / P _{op} μA/mW	0.5		100

Measurement Conditions / Comments
5 V

Parameter	Symbol	Unit	min	typ	max
Current	I _{TEC}	Α		0.4	
Voltage	U_{TEC}	V		1.3	
Power Dissipation (total loss at case)	P _{loss}	W		0.5	
Temperature Difference	ΔΤ	K			50

Measurement Conditions / Comments	
Popt = 80 mW, ΔT = 20 K	
Popt = 80 mW, ΔT = 20 K	
Popt = 80 mW, ΔT = 20 K	
Popt = 80 mW, ΔT = Tcase - TLD	

Themistor (Standard NTC Type)

Parameter	Symbol	Unit	min	typ	max
Resistance	R	kΩ		10	
Beta Coefficient	β			3892	
Steinhart & Hart Coefficient A	Α		1.	.1293 x 10 ⁻	3
Steinhart & Hart Coefficient B	В		2.	3410 x 10	4
Steinhart & Hart Coefficient C	С		8.	.7755 x 10	8

Measurement Conditions / Comments				
Tchip = 25° C				
$R_1/R_2 = e^{\beta}(1/T_1 - 1/T_2)$ at Tchip = 0° 50° C				
$1/T = A + B(\ln R) + C(\ln R)^3$				
T: Temperature in Kelvin				
R: resistance at T in Ω				

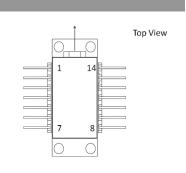


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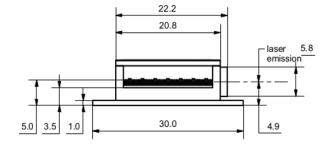
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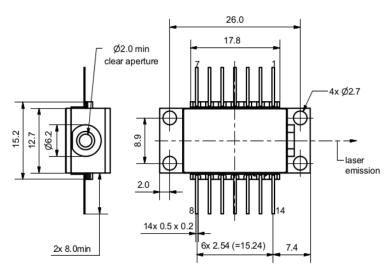


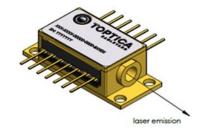
Pin Assignment					
	1	Thermoelectric Cooler (+)	14	Thermoelectric Cooler (-)	
	2	Thermistor	13	Case	
	3	Photo Diode Anode	12	not connected	
	4	Photo Diode Cathode	11	Laser Diode Cathode	
	5	Thermistor	10	Laser Diode Anode	
	6	not connected	9	not connected	
	7	not connected	8	not connected	



Package Drawings







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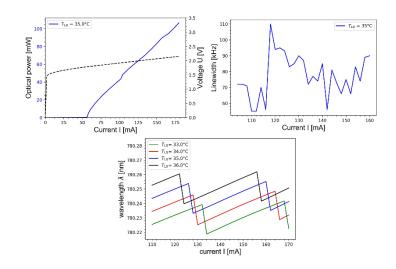
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Typical Measurement Results



Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.





A laser diode is sensitive against optical feedback, so an optical isolator may be required in order to avoid any disturbance of the emission spectrum. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.



IEC-60825-1

Avoid direct and/or indirect exposure to the free running beam. Collimating and focussing the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.





Complies with 21 CFR 1040.10 and 1040.40

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.